AMENDMENTS TO THE SPECIFICATION

Paragraph page 9, beginning line 25:

Reference is now made to Fig. 2. After the wafers 12 have been contacted by the etching solution 14 for a sufficient period of time, the upper wall component 22 is released and the upper wall component 22 pivotally rotates about the hinge 24. Once the upper wall component 22 is released, the liquid holding capacity of etching apparatus 10 is reduced, and the etching solution 14 rapidly flows from the etching bath apparatus 10 and into the outer weir 18 as indicated by the arrows.

Paragraph page 12, beginning line 20:

Fig. 7 is a cross-sectional view of the etching bath apparatus 110 as shown in Fig. 5. As can be seen from this figure, the wafers 112 are submerged in the etching solution 114. As the wafers are etched, surface contaminants 116 form at the air/liquid interface of the etching bath apparatus 110. As can be seen from Fig. 8, once the upper wall component 122 is released, the liquid holding capacity of etching apparatus 110 is reduced, and the etching solution 114 rapidly flows out of the etching bath apparatus 110. Since the flow rate of the etching solution 114 is significant due to the sudden release of the upper wall component 22, the surface tension and eddy current forces holding the contaminants 116 at the air/liquid interface are broken and the contaminants 116 flow into the outer weir 118 where they may be collected.

Paragraph on page 14, beginning line 5:

Reference is made to Fig. 10. After the wafers 212 have been contacted by the etching solution 214 for a sufficient period of time, the slideable door component 220 is released and the slideable door component 220 slides down the outer wall component 215, reducing the liquid holding capacity of etching bath apparatus 210, and rapidly releasing the etching solution 214, which rapidly flows into the outer weir 218 as indicated by the arrows.